

μ**PA1931**

MOS FIELD EFFECT TRANSISTOR

R07DS0009EJ0103 Rev.1.03 May 09, 2012

Description

The µPA1931 is a switching device, which can be driven directly by a 4.5 V power source.

The μ PA1931 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- 4.5 V drive available
- Low on-state resistance
 - $R_{DS(on)1} = 65 \text{ m}\Omega \text{ MAX}. (V_{GS} = -10 \text{ V}, I_D = -1.8 \text{ A})$
 - --- R_{DS(on)2} = 100 mΩ MAX. (V_{GS} = -4.5 V, I_D = -1.8 A)

Ordering Information

Part No.	Lead Plating	Packing	Package
μPA1931TE-T1-AT *1	Pure Sn (Tin)	Tape 3000 p/reel	SC-95 (Mini Mold Thin Type)
μPA1931TE-T2-AT *1			typ. 0.011 g

Note: *1 This product does not contain Pb.

"-T1" and "-T2" in Part No. indicate the unit orientation.

Marking: UB

Absolute Maximum Ratings $(T_A = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V_{DSS}	-40	V
Gate to Source Voltage (V _{DS} = 0 V)	V_{GSS}	∓20	V
Drain Current (DC) (T _A = 25°C)	I _{D(DC)}	∓4.5	А
Drain Current (pulse) *1	I _{D(pulse)}	∓18	А
Total Power Dissipation	P _{T1}	0.2	W
Total Power Dissipation *2	P _{T2}	2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	−55 to +150	°C
Single Avalanche Current *3	I _{AS}	3.5	А
Single Avalanche Energy *3	E _{AS}	1.2	mJ

Notes: *1 $P_W \le 10 \mu s$, Duty Cycle $\le 1\%$

^{*2} Mounted on FR-4 board of 50 mm \times 50 mm \times 1.6 mmt, t \leq 5 sec

^{*3} $T_{ch(peak)} \le 150$ °C, $R_G = 25 \Omega$

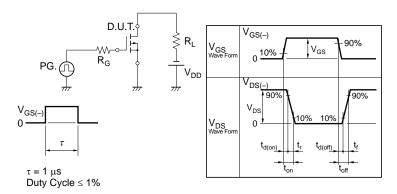
Electrical Characteristics $(T_A = 25^{\circ}C)$

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			-10	μΑ	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			∓20	μΑ	$V_{GS} = \mp 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	V _{GS(off)}	-1.0	-1.7	-2.5	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	2.5			S	$V_{DS} = -10 \text{ V}, I_D = -1.8 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		44	65	mΩ	$V_{GS} = -10 \text{ V}, I_D = -1.8 \text{ A}$
Resistance *1	R _{DS(on)2}		53	100	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -1.8 \text{ A}$
Input Capacitance	C _{iss}		880		pF	V _{DS} = −10 V
Output Capacitance	Coss		150		pF	$V_{GS} = 0 V$
Reverse Transfer Capacitance	C _{rss}		115		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		9		ns	$V_{DD} = -20 \text{ V}, I_D = -1.8 \text{ A}$
Rise Time	t _r		4		ns	V _{GS} = −10 V
Turn-off Delay Time	t _{d(off)}		74		ns	$R_G = 10 \Omega$
Fall Time	t _f		37		ns	
Total Gate Charge	Q_G		20		nC	V _{DD} = −32 V
Gate to Source Charge	Q_GS		3		nC	V _{GS} = −10 V
Gate to Drain Charge	Q_GD		5		nC	I _D = −3.5 A
Body Diode Forward Voltage *1	V _{F(S-D)}			1.5	V	I _F = 3.5 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		30		ns	I _F = 3.5 A, V _{GS} = 0 V
Reverse Recovery Charge	Q _{rr}		34		nC	di/dt = 100 A/μs

Note: *1 Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

TEST CIRCUIT 2 SWITCHING TIME

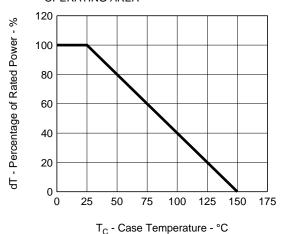


TEST CIRCUIT 3 GATE CHARGE

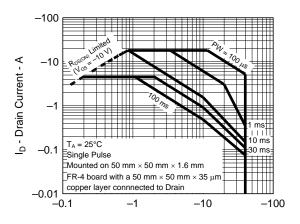
$$\begin{array}{c|c} \text{D.U.T.} \\ \text{I}_{G} = -2 \text{ mA} \\ \hline \\ \text{PG.} \\ \hline \\ \end{array} \begin{array}{c} \text{S} \\ \text{S} \\ \text{O} \\ \end{array} \begin{array}{c} \text{D.U.T.} \\ \\ \hline \\ \end{array} \begin{array}{c} \text{R}_{L} \\ \\ \hline \\ \end{array} \\ \begin{array}{c} \text{V}_{DD} \\ \\ \end{array}$$

Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

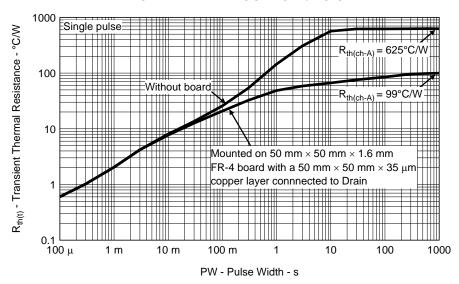


FORWARD BIAS SAFE OPERATING AREA

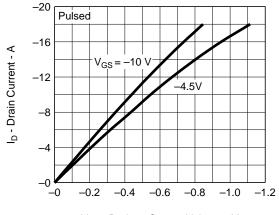


V_{DS} - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

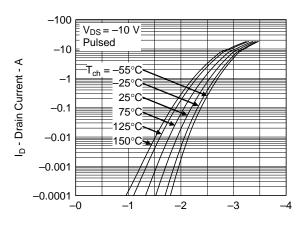


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



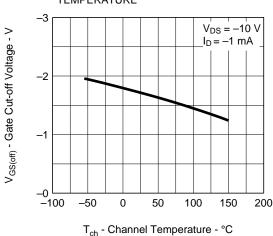
 $V_{\rm DS}$ - Drain to Source Voltage - V

FORWARD TRANSFER CHARACTERISTICS

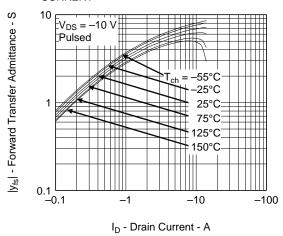


V_{GS} - Gate to Source Voltage - V

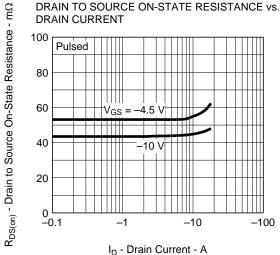
GATE CUT-OFF VOLTAGE vs. CHANNEL **TEMPERATURE**



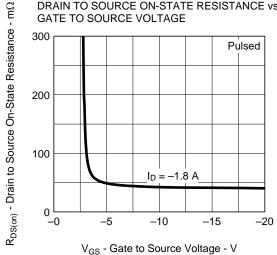
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



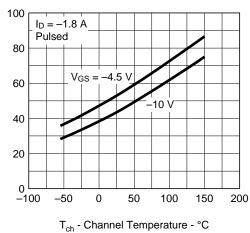
DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



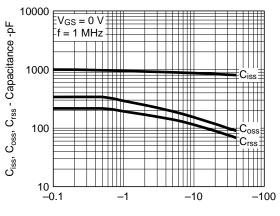
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

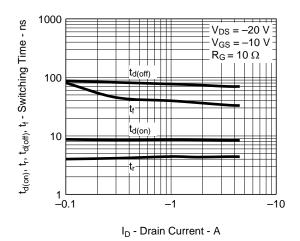


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

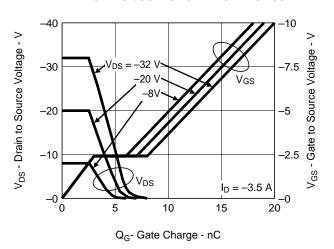


 $V_{\rm DS}$ - Drain to Source Voltage - V

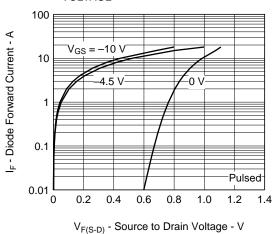
SWITCHING CHARACTERISTICS



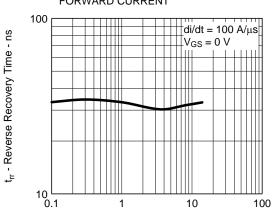
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



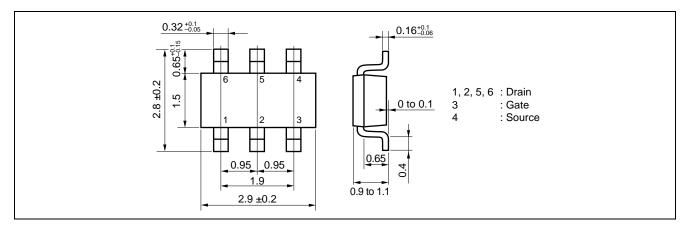
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



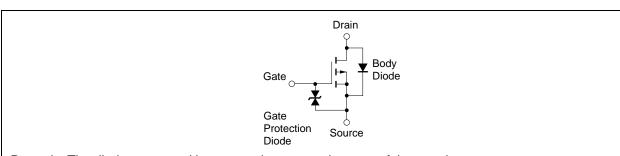
I_F - Diode Forward Current - A

Package Drawings (Unit: mm)

SC-95 (Mini Mold Thin Type)



Equivalent Circuit



Remark: The diode connected betweeen the gate and source of the transisor serves as a protector against EDS. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Revision History

μPA1931 Data Sheet

		Description		
Rev.	Date	Page	Summary	
1.00	Jun 01, 2010	_	First Edition Issued	
1.01	Oct 20, 2010	P1	Taping code corrected	
1.02	Mar 06, 2012	P1	A type in PT1 item name corrected.	
		P3	A type corrected in legend of "TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH" graph.	
1.03	May 09, 2012	P1, P2	Minor error correction of letters	

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